Specifications of the STAR-Silicon Vertex Tracker	
length (active area)	44.1 cm (max.)
η-*coverage*	± 1
Inner Barrel (radial distance)	5.97 cm
Middle Barrel (radial distance)	10.16 cm
Outer Barrel (radial distance)	14.91 cm
Thickness of wafer (SDD)	300 μm
Total Thickness	900 μm $\sim$ 0.9% X_o
Average Radiation Length (incl. FEE)	4.5%
Number of wafers	216
Inner Barrel	32 (8×4)
Middle Barrel	72 (12×6)
Outer Barrel	112 (16×7)
Diameter of wafer (SDD)	10.16 cm = 4 in
Length of wafer (SDD)	6.3 cm
Width of wafer (SDD)	6.3 cm
Drift Length on wafer	3 cm (max.)
Average Drift Time	5 μs
Maximum High Voltage	1500 V
Time Samples	128
Sampling Rate	25 MHz
Anode Pitch	250 μm
Number of Channels	103680
Position Resolution	< 25 μm